



April 2015

## FDBL0210N80

### N-Channel PowerTrench<sup>®</sup> MOSFET

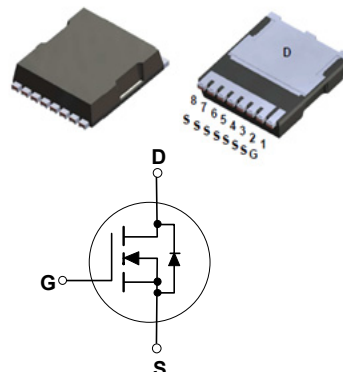
80 V, 240 A, 2.0 mΩ

#### Features

- Typical  $R_{DS(on)}$  = 1.5 mΩ at  $V_{GS}$  = 10V,  $I_D$  = 80 A
- Typical  $Q_{g(tot)}$  = 130 nC at  $V_{GS}$  = 10V,  $I_D$  = 80 A
- UIS Capability
- RoHS Compliant

#### Applications

- Industrial Motor Drive
- Industrial Power Supply
- Industrial Automations
- Battery Operated tools
- Battery Protection
- Solar Inverters
- UPS and Energy Inverters
- Energy Storage
- Load Switch



For current package drawing, please refer to the Fairchild web-site at <http://www.fairchildsemi.com/dwg/PS/PSOF08A.pdf>.

#### MOSFET Maximum Ratings $T_J = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain-to-Source Voltage	80	V
$V_{GS}$	Gate-to-Source Voltage	±20	V
$I_D$	Drain Current - Continuous ( $V_{GS}=10$ ) (Note 1)	$T_C = 25^\circ\text{C}$	A
	Pulsed Drain Current	$T_C = 25^\circ\text{C}$	
$E_{AS}$	Single Pulse Avalanche Energy (Note 2)	512	mJ
$P_D$	Power Dissipation	357	W
	Derate Above $25^\circ\text{C}$	2.38	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature	-55 to + 175	$^\circ\text{C}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.42	$^\circ\text{C/W}$
$R_{\theta JA}$	Maximum Thermal Resistance, Junction to Ambient (Note 3)	43	$^\circ\text{C/W}$

#### Notes:

- 1: Current is limited by silicon.
- 2: Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.25\text{mH}$ ,  $I_{AS} = 64\text{A}$ ,  $V_{DD} = 80\text{V}$  during inductor charging and  $V_{DD} = 0\text{V}$  during time in avalanche.
- 3:  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design, while  $R_{\theta JA}$  is determined by the board design. The maximum rating presented here is based on mounting on a 1 in<sup>2</sup> pad of 2oz copper.

#### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDBL0210N80	FDBL0210N80	MO-299A	-	-	-

**Electrical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
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**Off Characteristics**

$B_{V_{DS}}$	Drain-to-Source Breakdown Voltage	$I_D = 250\mu\text{A}$ , $V_{GS} = 0\text{V}$	80	-	-	V
$I_{DSS}$	Drain-to-Source Leakage Current	$V_{DS} = 80\text{V}$ , $T_J = 25^\circ\text{C}$ $V_{GS} = 0\text{V}$ , $T_J = 175^\circ\text{C}$ (Note 4)	-	-	1	$\mu\text{A}$
$I_{GSS}$	Gate-to-Source Leakage Current	$V_{GS} = \pm 20\text{V}$	-	-	$\pm 100$	nA

**On Characteristics**

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\mu\text{A}$	2.0	3.0	4.0	V
$R_{DS(on)}$	Drain to Source On Resistance	$I_D = 80\text{A}$ , $T_J = 25^\circ\text{C}$	-	1.5	2.0	$\text{m}\Omega$
		$V_{GS} = 10\text{V}$ , $T_J = 175^\circ\text{C}$ (Note 4)	-	3.1	4.1	$\text{m}\Omega$

**Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V, f = 1MHz		-	10000	-	pF
C <sub>oss</sub>	Output Capacitance			-	1540	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			-	70	-	pF
R <sub>g</sub>	Gate Resistance	f = 1MHz		-	2.8	-	Ω
Q <sub>g(ToT)</sub>	Total Gate Charge at 10V	V <sub>GS</sub> = 0 to 10V	V <sub>DD</sub> = 64V I <sub>D</sub> = 80A	-	130	169	nC
Q <sub>g(th)</sub>	Threshold Gate Charge	V <sub>GS</sub> = 0 to 2V		-	18	27	nC
Q <sub>gs</sub>	Gate-to-Source Gate Charge			-	47	-	nC
Q <sub>gd</sub>	Gate-to-Drain "Miller" Charge			-	24	-	nC

**Switching Characteristics**

$t_{on}$	Turn-On Time	$V_{DD} = 40\text{V}$ , $I_D = 80\text{A}$ , $V_{GS} = 10\text{V}$ , $R_{GEN} = 6\Omega$	-	-	133	ns
$t_{d(on)}$	Turn-On Delay		-	39	-	ns
$t_r$	Rise Time		-	63	-	ns
$t_{d(off)}$	Turn-Off Delay		-	61	-	ns
$t_f$	Fall Time		-	33	-	ns
$t_{off}$	Turn-Off Time		-	-	140	ns

**Drain-Source Diode Characteristics**

$V_{SD}$	Source-to-Drain Diode Voltage	$I_{SD} = 80\text{A}$ , $V_{GS} = 0\text{V}$	-	-	1.25	V
		$I_{SD} = 40\text{A}$ , $V_{GS} = 0\text{V}$	-	-	1.2	V
$t_{rr}$	Reverse-Recovery Time	$I_F = 80\text{A}$ , $dI_{SD}/dt = 100\text{A}/\mu\text{s}$ , $V_{DD} = 64\text{V}$	-	83	108	ns
$Q_{rr}$	Reverse-Recovery Charge		-	118	153	nC

**Note:**

4: The maximum value is specified by design at  $T_J = 175^\circ\text{C}$ . Product is not tested to this condition in production.

## Typical Characteristics

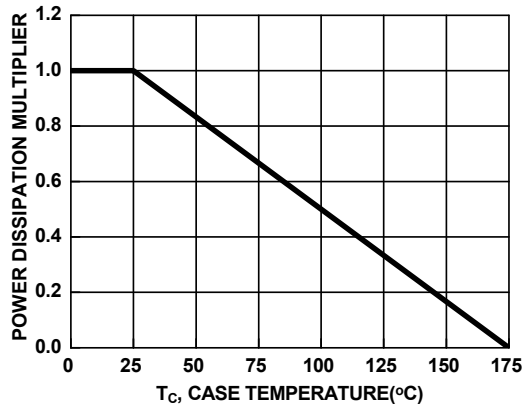


Figure 1. Normalized Power Dissipation vs. Case Temperature

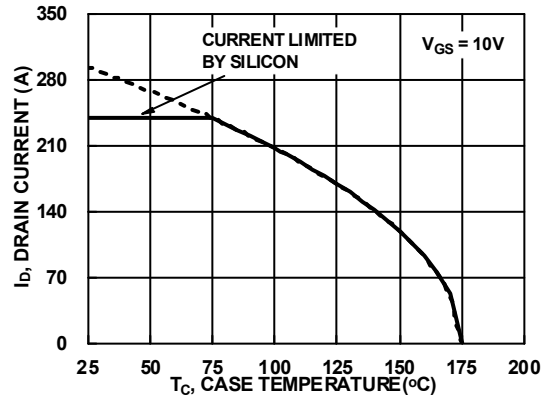


Figure 2. Maximum Continuous Drain Current vs. Case Temperature

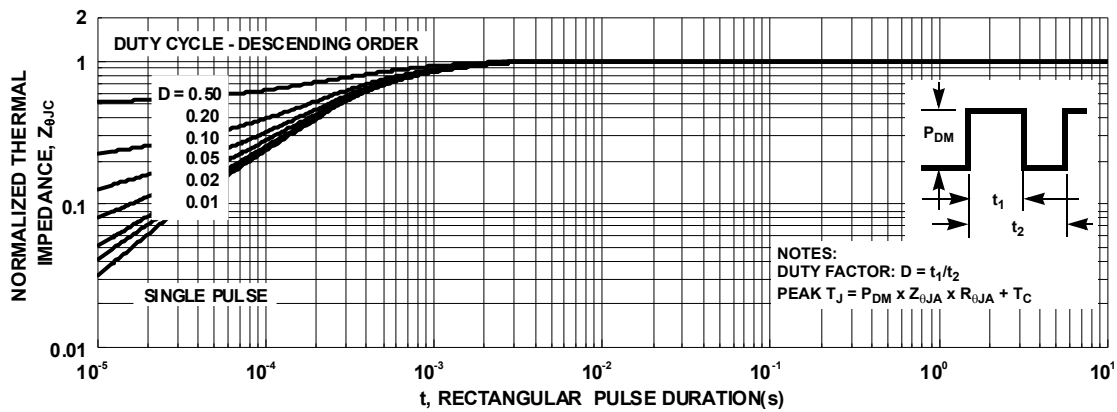


Figure 3. Normalized Maximum Transient Thermal Impedance

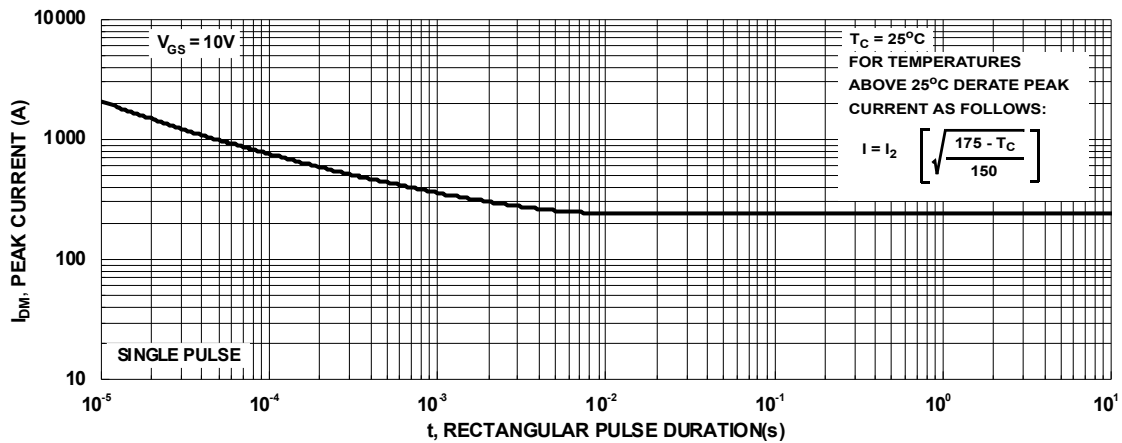


Figure 4. Peak Current Capability

## Typical Characteristics

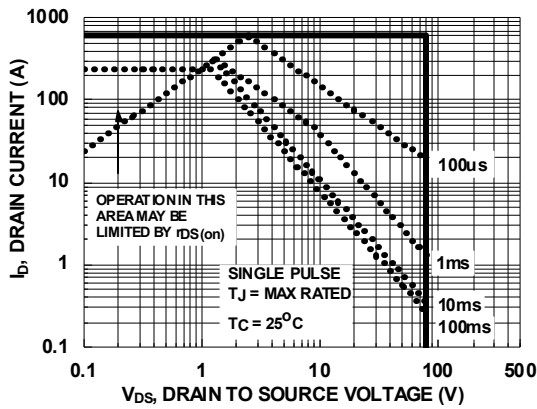
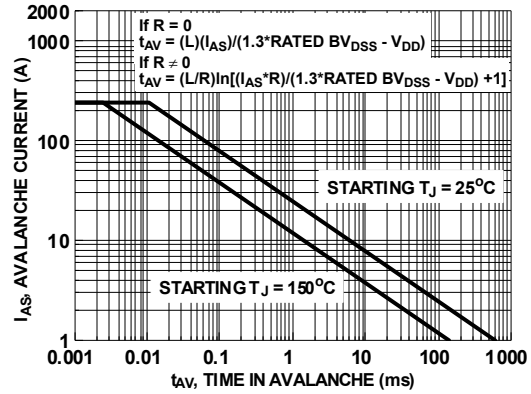


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to Fairchild Application Notes AN7514 and AN7515

Figure 6. Unclamped Inductive Switching Capability

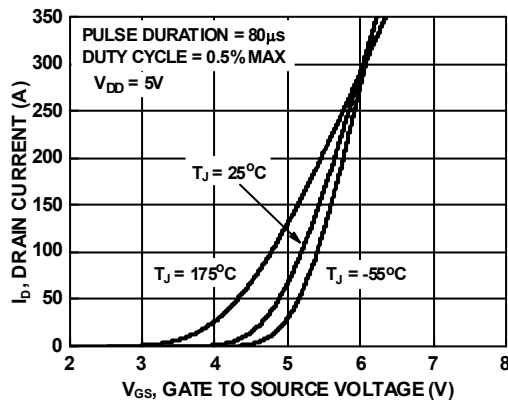


Figure 7. Transfer Characteristics

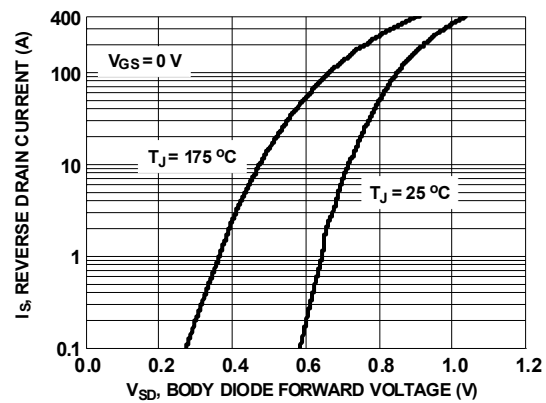


Figure 8. Forward Diode Characteristics

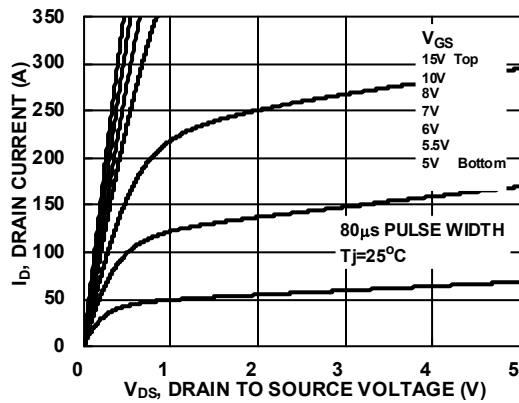


Figure 9. Saturation Characteristics

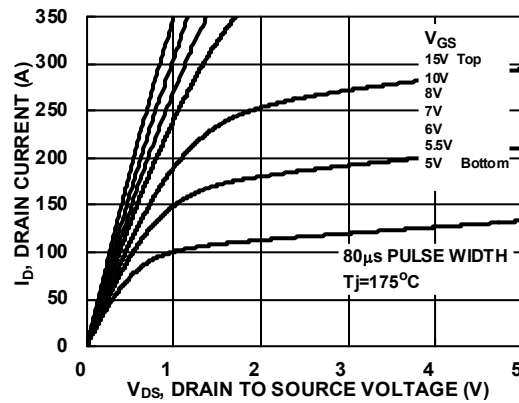


Figure 10. Saturation Characteristics

## Typical Characteristics

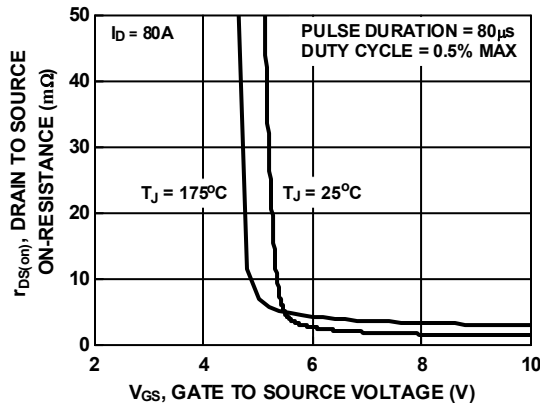


Figure 11.  $R_{DS(on)}$  vs. Gate Voltage

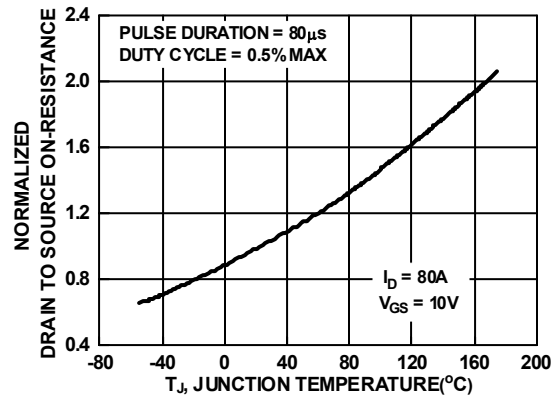


Figure 12. Normalized  $R_{DS(on)}$  vs. Junction Temperature

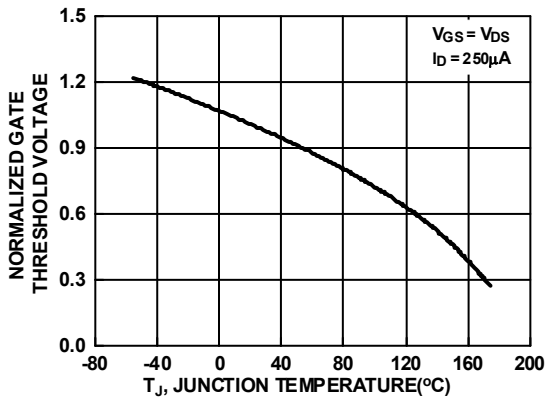


Figure 13. Normalized Gate Threshold Voltage vs. Temperature

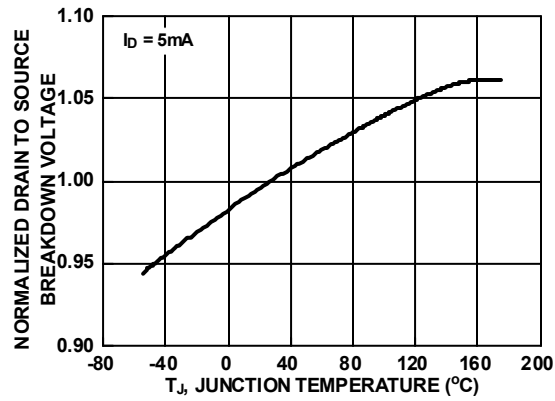


Figure 14. Normalized Drain to Source Breakdown Voltage vs. Junction Temperature

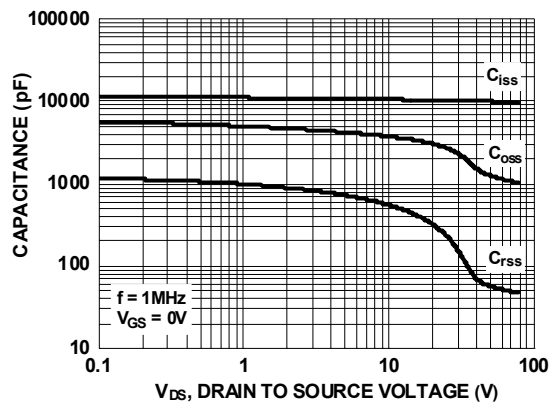


Figure 15. Capacitance vs. Drain to Source Voltage

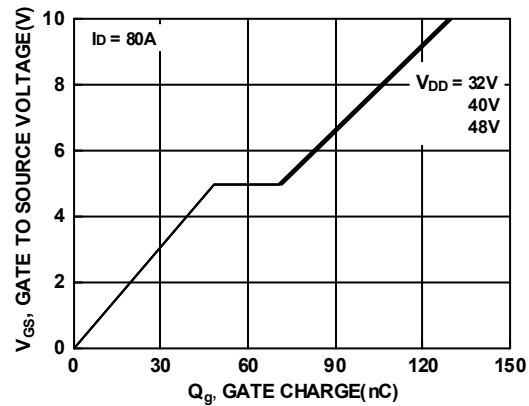
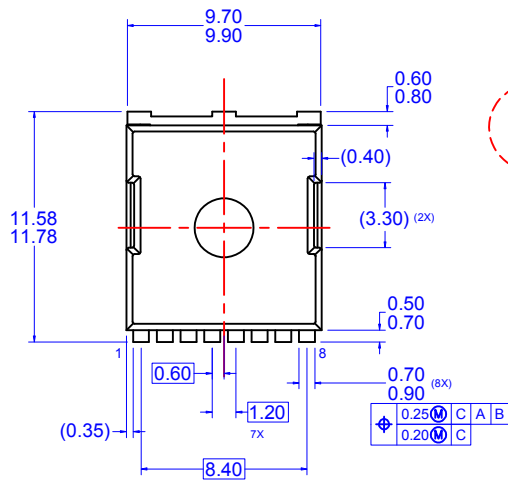
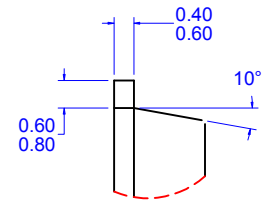
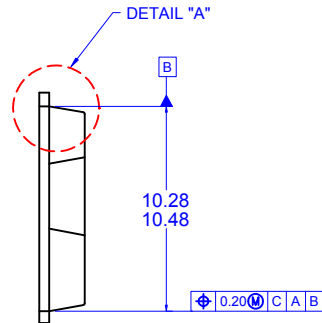


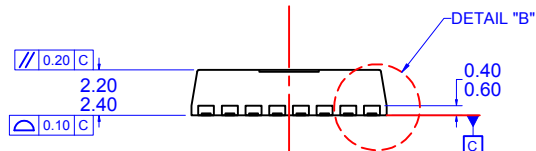
Figure 16. Gate Charge vs. Gate to Source Voltage



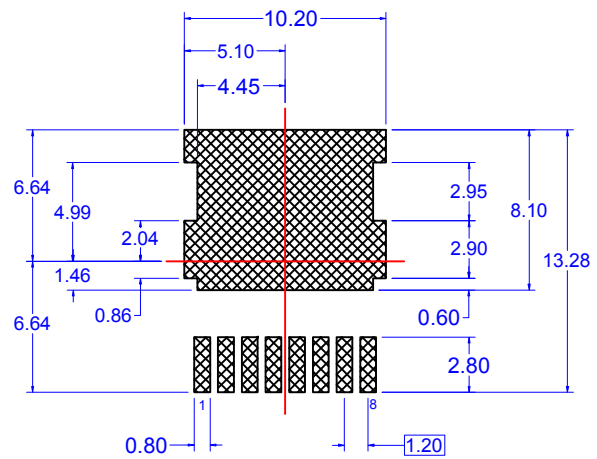
TOP VIEW



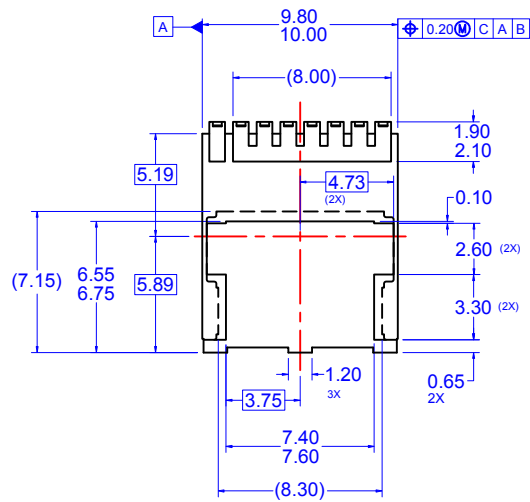
DETAIL "A"



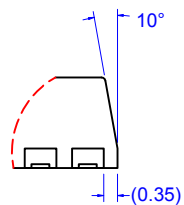
SIDE VIEW



LAND PATTERN  
RECOMMENDATION



BOTTOM VIEW



DETAIL "B"

- NOTES: UNLESS OTHERWISE SPECIFIED
- A) PACKAGE STANDARD REFERENCE:  
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  - B) ALL DIMENSIONS ARE IN MILLIMETERS.
  - C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
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  - E) DRAWING FILE NAME: MKT-PSOF08AREV3

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